

Meera Chandrasekhar

List of Publications by Year in descending order

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26
papers

1,466
citations

516561

16
h-index

580701

25
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all docs

27
docs citations

27
times ranked

915
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of mobile technology-based physics curriculum on preservice elementary teachers' technology self-efficacy. <i>Science Education</i> , 2020, 104, 252-289.	1.8	14
2	Pressure Raman effects and internal stress in network glasses. <i>Physical Review B</i> , 2005, 71, .	1.1	121
3	Temperature dependence of strain in ZnSe(epilayer)/GaAs(epilayer). <i>Journal of Applied Physics</i> , 1995, 78, 6569-6573.	1.1	17
4	Optical studies of strained pseudomorphic semiconductor heterostructures under external pressure. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1994, 70, 369-380.	0.6	23
5	Raman and modulated-reflectivity spectra of a strained pseudomorphic ZnTe epilayer on InAs under pressure. <i>Physical Review B</i> , 1994, 49, 2181-2184.	1.1	22
6	Pressure tuning of strain in CdTe/InSb epilayer: A photoluminescence and photomodulated reflectivity study. <i>Journal of Applied Physics</i> , 1993, 74, 4136-4144.	1.1	15
7	Electronic transitions in semiconductor quantum wells and epilayers under pressure. <i>High Pressure Research</i> , 1992, 9, 57-82.	0.4	17
8	Pressure tuning of strains in semiconductor heterostructures: (ZnSe epilayer)/(GaAs epilayer). <i>Physical Review B</i> , 1991, 44, 11307-11314.	1.1	76
9	Electronic transitions in bulk Al _{0.3} Ga _{0.7} As under hydrostatic pressure. <i>Physical Review B</i> , 1991, 44, 13404-13417.	1.1	11
10	Deep center in Al _{0.3} Ga _{0.7} As. <i>Physical Review B</i> , 1991, 43, 12126-12129.	1.1	3
11	Photoreflectance studies of electronic transitions in quantum well structures under high pressure. , 1990, , .		4
12	Electronic transitions in CdTe under pressure. <i>Physical Review B</i> , 1990, 42, 3586-3590.	1.1	27
13	Spectroscopic studies of strained-layer GaSb—AlSb superlattices. <i>Surface Science</i> , 1990, 228, 322-325.	0.8	9
14	Quantum wells and deep impurity levels under hydrostatic pressure. <i>Superlattices and Microstructures</i> , 1988, 4, 107-114.	1.4	8
15	High-pressure studies of GaAs-Ga _{1-x} Al _x As quantum wells of widths 26 to 150 Å. <i>Physical Review B</i> , 1986, 33, 8416-8423.	1.1	171
16	Photoluminescence studies of a GaAs-Ga _{1-x} Al _x As superlattice at 8–300 K under hydrostatic pressure (0–70 kbar). <i>Physical Review B</i> , 1985, 31, 4106-4109.	1.1	62
17	Low-temperature studies of the photoluminescence in CdS under hydrostatic pressure. <i>Physical Review B</i> , 1985, 31, 1219-1222.	1.1	25
18	Effects of hydrostatic pressure on the low-temperature photoluminescence spectrum of heavily doped CdS. <i>Physical Review B</i> , 1985, 31, 6574-6578.	1.1	6

#	ARTICLE	IF	CITATIONS
19	Pressure-induced shifts of the fluorescence spectrum of rhodamine 6G in solution. Applied Optics, 1985, 24, 2779.	2.1	12
20	Luminescence and Raman spectra of CdS under hydrostatic pressure. Physical Review B, 1984, 30, 3316-3319.	1.1	44
21	Study of the localized vibrations of boron in heavily doped Si. Physical Review B, 1980, 22, 4825-4833.	1.1	88
22	A new method to measure stress-induced birefringence in an opaque material: Stress-induced Raman scattering. Journal of the Optical Society of America, 1978, 68, 523.	1.2	10
23	Effects of interband excitations on Raman phonons in heavily doped n^+Si . Physical Review B, 1978, 17, 1623-1633.	1.1	232
24	Piezobirefringence above the fundamental edge in Si. Physical Review B, 1978, 18, 4301-4311.	1.1	39
25	Intraband Raman scattering by free carriers in heavily doped n^+Si . Physical Review B, 1977, 16, 3579-3595.	1.1	59
26	Effects of uniaxial stress on the electroreflectance spectrum of Ge and GaAs. Physical Review B, 1977, 15, 2127-2144.	1.1	351